

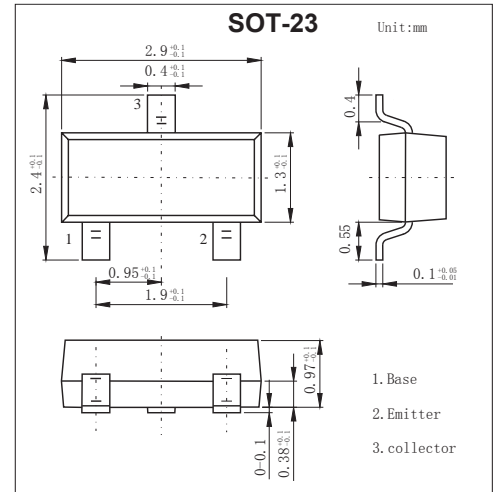
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Complementary to 2SC1623
- High DC Current Gain: $h_{FE}=200$ TYP. ($V_{CE}=-6V, I_C=-1mA$)
- High Voltage: $V_{ce0}=-50V$
- PNP TRANSISTORS
- Collector-Base Voltage: $V_{CBO}=-60V$

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-100	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SA812	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-1mA$	90		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.3	V
Base-emitter voltage	V_{BE}	$I_C=-1mA, V_{CE}=-6V$	-0.58		-0.68	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-10mA$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4.5		pF

CLASSIFICATION OF h_{FE}

Rank	M4	M5	M6	M7
Range	90-180	135-270	200-400	300-600
Marking	M4	M5	M6	M7

Typical Characteristics

